#### **Supplementary Information**

# Doping Effect of Antimony on $^{BaFeO}{}_3$ Perovskite Oxide: Optical, Electronic, Magnetic and Thermoelectric Properties

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#### **Supplementary Methods:**

### 1.1. Volume Optimization: Calculation Methods

The equation presented is a form of the Birch-Murnaghan equation of state[1], which is commonly used to fit the energy vs volume (E vs V) data obtained from first-principles calculations. It provides valuable insights into the mechanical properties of materials under hydrostatic pressure. Hence the fitting Birch-Murnaghan equation equation given by,

$$E(V) = E_0 + \frac{B_0 \cdot V}{[B_0 \cdot (B_0 - 1)]} \cdot \left[ \left( \frac{V_0}{V} \right)^{(B_0 - 1)} + (B_0 - 1) \right] - \frac{B_0 V_0}{B_0 - 1}$$
(1)

Where E(V) denotes the total energy at a given volume V,  $E_0$  represents the minimum energy corresponding to the equilibrium volume  $V_0$ , The parameter  $B_0$  is the bulk modulus at equilibrium, reflecting the material's resistance to volume change under applied pressure. The term  $B_0$  is the first derivative of the bulk modulus with respect to pressure, indicating how the

compressibility of the material evolves under increasing pressure. The ratio  $\left(\frac{V_0}{V}\right)^{(B'_0-1)}$  describes the non-linear change in energy with respect to compression or expansion.

Volume optimization of Pure BaFeO<sub>3</sub>

Volume (Bohr³)	ΔVol (%)	Total Energy (Ry)
401.43966	-5.00	-19276. 15450501
405.66542	-4.00	-19276. 15630557
409.89109	-3.00	-19276. 15743921
414.11668	-2.00	-19276. 15810981

418.34234	-1.00	-19276. 15832588
422.56810	0.00	-19276. 15806284
426.79382	1.00	-19276. 15756652
431.01954	2.00	-19276. 15668103
435.24516	3.00	-19276. 15535176
439.47090	4.00	-19276. 15355434
443.69651	5.00	-19276. 15164043

Where,

= 418.34234 Bohr^3 Volume Minimum energy = -19276.15832588 Ry Change in volume = -1.00 %

## Volume optimization of 12.5% Sb- doped BaFeO<sub>3</sub>

Volume (Bohr³)	ΔVol (%)	Total Energy (Ry)
3211.517	-5	-164630. 75647872
3245.323	-4	-164630. 78031558
3279.129	-3	-164630. 80098508
3312.934	-2	-164630. 81692826
3346.739	-1	-164630. 82906511
3380.545	0	-164630. 83640005
3414.351	1	-164630. 84234781
3448.156	2	-164630. 84481484
3481.961	3	-164630. 84404520
3515.767	4	-164630. 83995004
3549.572	5	-164630. 83316549
3583.377	6	-164630. 82332920
3617.183	7	-164630. 81188272

Where,

Volume = 3448.15567 Bohr^3

Minimum energy = -164630.84481484 Ry

Change in volume = 2.00 %

# Volume optimization of 25% Sb- doped BaFeO<sub>3</sub>

Volume (Bohr³)	ΔVol (%)	Total Energy (Ry)
3199.9557	-5	-175052.26743460
3233.63938	-4	-175052.30382875
3267.32345	-3	-175052.33733845
3301.00717	-2	-175052.36504879
3334.69058	-1	-175052.38896332
3368.37449	0	-175052.40737160
3402.05849	1	-175052.42318450
3435.74226	2	-175052.43459231
3469.42555	3	-175052.44232088
3503.1096	4	-175052.44757688
3536.793	5	-175052.44960388

3570.47717	6	-175052.44816678
3604.16085	7	-175052.44449742
3637.84424	8	-175052.43789815
3671.52836	9	-175052.42944722
3705.21217	10	-175052.41856316

Where,

Volume =  $3536.79300 \text{ Bohr}^3$ 

Minimum energy = -175052.44960388 Ry

Change in volume = 5.00 %

## 1.2. Optical Constants: Calculation Methods

The dielectric function's real and imaginary parts can be used to determine the optical behavior of a material. For crystalline solids, the complex dielectric function, dependent on frequency, is expressed as:

$$\varepsilon(\omega) = \varepsilon_1(\omega) + i\varepsilon_2(\omega) \tag{2}$$

where  $\varepsilon_1(\omega)$  represents the material's dispersive properties (i.e. real part), and  $\varepsilon_2(\omega)$  accounts for absorption effects (i.e. imaginary part). In cartesian coordinates,

$$\varepsilon(\omega) = \begin{pmatrix} \varepsilon_{xx}(\omega) & \varepsilon_{xy}(\omega) & \varepsilon_{xz}(\omega) \\ \varepsilon_{yx}(\omega) & \varepsilon_{yy}(\omega) & \varepsilon_{yz}(\omega) \\ \varepsilon_{zx}(\omega) & \varepsilon_{zy}(\omega) & \varepsilon_{zz}(\omega) \end{pmatrix}$$
(3)

At long-wavelength infrared (LWIR) wavelengths, intra-band transitions play a crucial role. Therefore, the overall dielectric function can be represented by the combined effect of interband ( $\varepsilon^{inter}(\omega)$ ) and intra-band transitions ( $\varepsilon^{intra}(\omega)$ ), respectively. And this is represented by the following expression,

$$\varepsilon(\omega) = \varepsilon^{inter}(\omega) + \varepsilon^{intra}(\omega) \tag{4}$$

First-order time-dependent perturbation theory allows for the derivation of the inter-band component of the dielectric function [4]. It is given by the following expression:

$$\varepsilon_{\alpha\beta}^{inter}(\omega) = 1 - \frac{8\pi e^2}{\Omega} \sum_{k,v,c} \frac{\left\langle \psi_{k+qe_{\alpha}}^{c} \left| e^{iq.r} \left| \psi_{k}^{v} \right\rangle \left\langle \psi_{k}^{v} \right| e^{-iq.r} \left| \psi_{k+qe_{\beta}}^{c} \right\rangle \right\rangle}{\left(E_{k+q}^{c} - E_{k}^{v} - \hbar\omega - i\hbar\alpha\right)} + CC$$
 (5)

In this formulation,  $\omega$  symbolizes the phonon frequency, while  $\Omega$  represents the volume of a single unit cell. The elementary charge of an electron is represented by e and r defines the position vector. The parameter q captures the photon momentum. Furthermore,  $E_k^v$  and  $E_k^c$  correspond to the wavefunctions of electrons in the valence and conduction bands at a specific wavevector k. In computational approaches, the dielectric function's imaginary part is typically

evaluated through numerical methods, and the real component is subsequently determined using the Kramers-Kronig relation, as shown below,

$$\varepsilon_{1}^{inter}(\omega) = 1 + \frac{2}{\pi} P \int_{0}^{\infty} \frac{\omega' \varepsilon^{inter}(\omega') d\omega'}{\omega' - \omega^{2}}.$$
 (6)

In addition, the intra-band contributions to the dielectric function are analyzed with the help of the free-electron plasma model, which is represented by,

$$\varepsilon^{inter}(\omega) = 1 - \frac{\omega_p^2}{\omega(\omega + i\gamma)} \tag{7}$$

Here, the plasma frequency  $(^{\omega}p)$  is determined using Density Functional Theory (DFT) calculations. Herein, The inverse lifetime  $(\gamma)$  may vary from 0 to 1 eV [5] and the complex optical conductivity  $(\omega)$  is established based on the following relation:

$$\sigma(\omega) = -i\frac{\omega}{4\pi} [\varepsilon(\omega) - 1] \tag{8}$$

However, the extinction coefficient  $K(\omega)$ , The absorbance coefficient  $I(\omega)$ , the energy loss function  $L(\omega)$ , refractive index  $n(\omega)$ , the reflectivity coefficient  $r(\omega)$ , and the dielectric function  $\varepsilon(\omega)$ , including its real  $\varepsilon_1(\omega)$ , and imaginary  $\varepsilon_2(\omega)$  parts can be determined with the help of the following equations [6]:

$$K(\omega) = \frac{I(\omega)}{2\omega} \tag{9}$$

$$I(\omega) = \sqrt{2}\omega \left(\sqrt{\varepsilon_1(\omega)^2 + \varepsilon_2(\omega)^2} - \varepsilon_1(\omega)\right)^{1/2}$$
 (10)

$$L(\omega) = \frac{E}{(\varepsilon_1(\omega)^2 + \varepsilon_2(\omega)^2)}$$
(11)

$$r(\omega) = \frac{n + iK - 1}{n + iK + 1} \tag{12}$$

$$n(\omega) = \left(\frac{1}{\sqrt{2}}\right) \left(\sqrt{\varepsilon_1(\omega)^2 + \varepsilon_2(\omega)^2} - \varepsilon_1(\omega)\right)^{1/2}$$
 (13)

$$\varepsilon_1(\omega) = n^2 - K^2 \tag{14}$$

$$\varepsilon_2(\omega) = 2nK \tag{15}$$

$$\sqrt{\varepsilon(\omega)} = n(\omega) + iK_{(\omega)} \tag{16}$$

## 1.3. Magnetic moments: Calculation Methods

The total magnetic moment given by the following equation[7],

$$M_{tol} = \sum_{i} M_{i}^{\uparrow} - M_{i}^{\downarrow} + M_{interstitial}$$
 (17)

Where,

 $M_i^{\dagger}$  and  $M_i^{\dagger}$  are the spin-up and spin-down electron populations inside the muffin- tin sphere of atom i.

*M*<sub>interstitial</sub> is the spin density contribution from the interstitial region.

## 1.4. Thermoelectric properties: Calculation Methods

The performance of thermoelectric materials is commonly evaluated using the dimensionless figure of merit [7],

$$ZT = \frac{S^2 \sigma T}{\kappa} = \frac{S^2 \sigma T}{\kappa_e + \kappa_L} \tag{18}$$

where T is the absolute temperature,  $\sigma$  is the electrical conductivity, S is the Seebeck coefficient, and  $S^2\sigma$  is the power factor (PF). Also,  $k_e$  represents the thermal conductivity contributed by electrons and holes, while  $k_L$  denotes the thermal conductivity arising from phonons propagating through the crystal lattice [8].

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